

Abstract

BONDING WIRE FOR SEMICONDUCTOR DEVICE

The present invention provides a bonding wire for a semiconductor device suitable for cutting-edge high-density LSIs and on-vehicle LSIs by improving the formation rate of Cu-Al IMC in ball bonds. A bonding wire for a semiconductor device contains Pt of 0.1 mass% to 1.3 mass%, at least one dopant selected from a first dopant group consisting of In, Ga, and Ge, for a total of 0.05 mass% to 1.25 mass%, and a balance being made up of Cu and incidental impurities.